Rochester Electronics

Datasheet

PART NUMBER

D27512-25-ROCV

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All re-creations are done with the approval of the Original Component Manufacturer. (OCM)

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
    - Class Q Military
    - Class V Space Level

Qualified Suppliers List of Distributors (QSLD)

- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OCM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

27512
512K (64K x 8) PRODUCTION AND UV ERASABLE PROM

- **Software Carrier Capability**
- **170 ns Maximum Access Time**
- **Two-Line Control**
- **Int$_e$ligent Identifier™ Mode**
  — Automated Programming Operations
- **TTL Compatible**
- **Low Power**
  — 125 mA max. Active
  — 40 mA max. Standby
- **Int$_e$ligent Programming™ Algorithm**
- **Available in 28-Pin Cerdip**
  (See packaging spec order #231369)

The Intel 27512 is a 5V-only, 524,288-bit ultraviolet Erasable and Electrically Programmable Read Only Memory (EPROM) organized as 64K words by 8 bits. This ensures compatibility with high-performance microprocessors, such as the Intel 8 MHz iAPX 286, allowing full speed operation without the addition of performance-degrading WAIT states. The 27512 is also directly compatible with Intel's 8051 family of microcontrollers.

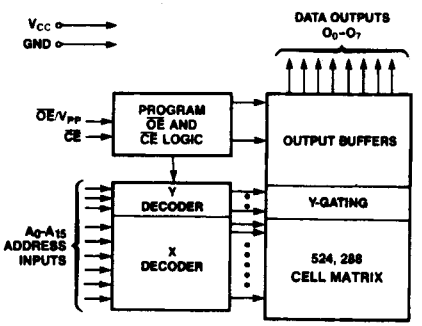
The 27512 enables implementation of new, advanced systems with firmware intensive architectures. The combination of the 27512's high-density, cost-effective EPROM storage, and new advanced microprocessors having megabyte addressing capability provides designers with opportunities to engineer user-friendly, high-reliability, high-performance systems.

The 27512's large storage capability of 64 K-bytes enables it to function as a high-density software carrier. Entire operating systems, diagnostics, high-level language programs and specialized application software can reside in a 27512 EPROM directly on a system's memory bus. This permits immediate microprocessor access and execution of software and eliminates the need for time-consuming disk accesses and downloads.

Two-line control and JEDEC-approved, 28-pin packaging are standard features of all Intel high-density EPROMs. This assures easy microprocessor interfacing and minimum design efforts when upgrading, adding, or choosing between nonvolatile memory alternatives.

The 27512 is manufactured using Intel's advanced HMOS *II-E technology.

*HMOS is a patented process of Intel Corporation.



231088-1

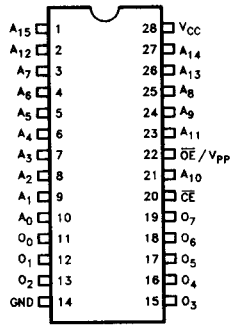
Figure 1. Block Diagram

October 1989
Order Number: 231088-007

Pin Names

A_0–A_{15}	Addresses
$\overline{CE}$	Chip Enable
$\overline{OE}/V_{PP}$	Outputs Enable/V_{PP}
O_0–O_7	Outputs
D.U.	Don't Use

27256 27C256	27128A 27C128	2764A 27C64 87C64	2732A	2716
V_{PP}	V_{PP}	V_{PP}		
A_{12}	A_{12}	A_{12}		
A_7	A_7	A_7	A_7	A_7
A_6	A_6	A_6	A_6	A_6
A_5	A_5	A_5	A_5	A_5
A_4	A_4	A_4	A_4	A_4
A_3	A_3	A_3	A_3	A_3
A_2	A_2	A_2	A_2	A_2
A_1	A_1	A_1	A_1	A_1
A_0	A_0	A_0	A_0	A_0
O_0	O_0	O_0	O_0	O_0
O_1	O_1	O_1	O_1	O_1
O_2	O_2	O_2	O_2	O_2
GND	GND	GND	GND	GND



231088-2

2716	2732A	2764A 27C64 87C64	27128 27128A	27256 27C256
		V_{CC}	V_{CC}	V_{CC}
		$\overline{PGM}$	$\overline{PGM}$	A_{14}
V_{CC}	V_{CC}	N.C.	A_{13}	A_{13}
A_8	A_8	A_8	A_8	A_8
A_9	A_9	A_9	A_9	A_9
V_{PP}	A_{11}	A_{11}	A_{11}	A_{11}
$\overline{OE}$	$\overline{OE}/V_{PP}$	$\overline{OE}$	$\overline{OE}$	$\overline{OE}$
A_{10}	A_{10}	A_{10}	A_{10}	A_{10}
$\overline{CE}$	$\overline{CE}$	$\overline{CE}$ ALE/$\overline{CE}$	$\overline{CE}$	$\overline{CE}$
O_7	O_7	O_7	O_7	O_7
O_6	O_6	O_6	O_6	O_6
O_5	O_5	O_5	O_5	O_5
O_4	O_4	O_4	O_4	O_4
O_3	O_3	O_3	O_3	O_3

Figure 2. Pin Configurations

EXTENDED TEMPERATURE (EXPRESS) EPROMs

The Intel EXPRESS EPROM family is a series of electrically programmable read only memories which have received additional processing to enhance product characteristics. EXPRESS processing is available for several densities of EPROM, allowing the choice of appropriate memory size to match system applications. EXPRESS EPROM products are available with 168 ±8 hours, 125°C dynamic burn-in using Intel's standard bias configuration. This process exceeds or meets most industry specifications of burn-in. The standard EXPRESS EPROM operating temperature range is 0°C to 70°C. Extended operating temperature range (−40°C to +85°C) EXPRESS products are available. Like all Intel EPROMs, the EXPRESS EPROM family is inspected to 0.1% electrical AQL. This may allow the user to reduce or eliminate incoming inspection testing.

EXPRESS EPROM PRODUCT FAMILY

PRODUCT DEFINITIONS

Type	Operating Temperature	Burn-in 125°C (hr)
Q	0°C to +70°C	168 ±8
T	−40°C to +85°C	None
L	−40°C to +85°C	168 ±8

EXPRESS OPTIONS

27512 VERSIONS

Packaging Options	
Speed Versions	**Cerdip**
-2	Q
-STD, -25, -30	Q, T, L
-3	L

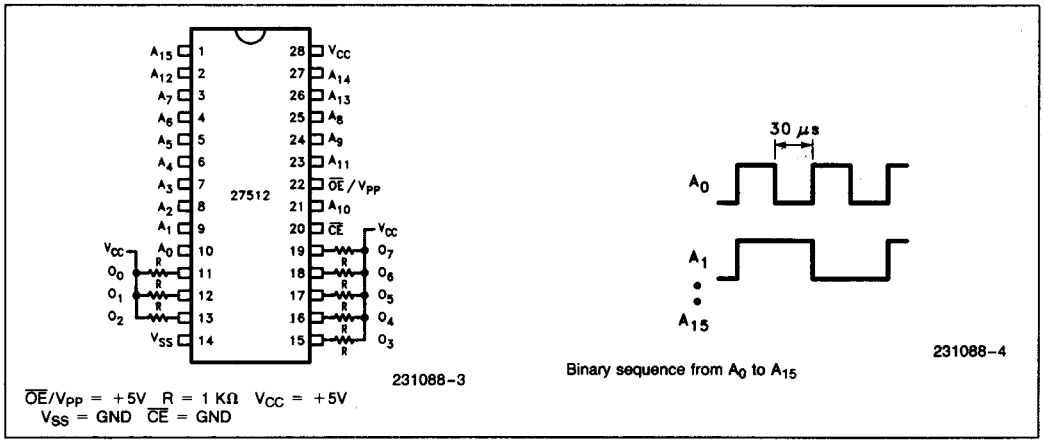
READ OPERATION

D.C. CHARACTERISTICS

Electrical parameters of EXPRESS EPROM products are identical to standard EPROM parameters except for:

Symbol	Parameter	TD27512 LD27512		Test Conditions
		Min	Max	
I_{SB}	V_{CC} Standby Current (mA)		50	$\overline{CE} = V_{IH}$, $\overline{OE}/V_{PP} = V_{IL}$
I_{CC1}(1)	V_{CC} Active Current (mA)		150	$\overline{OE}/V_{PP} = \overline{CE} = V_{IL}$
	V_{CC} Active Current at High Temperature (mA)		125	$\overline{OE}/V_{PP} = \overline{CE} = V_{IL}$ $T_{Ambient} = 85°C$

NOTE:
1. The maximum current value is with outputs O_0 to O_7 unloaded.



Burn-In Bias and Timing Diagrams

ABSOLUTE MAXIMUM RATINGS*

Operating Temperature during Read . . . . 0°C to 70°C
Temperature Under Bias . . . . . −10°C to +80°C
Storage Temperature . . . . . −65°C to +125°C
All Input or Output Voltages with Respect to Ground . . . . . −0.6V to +6.5V
Voltage on Pin 24 with Respect to Ground . . . . . −0.6V to +13.5V
$\overline{OE}/V_{PP}$ Supply Voltage with Respect to Ground . . . . . −0.6V to +14.0V
V_{CC} Supply Voltage with Respect to Ground . . . . . −0.6V to +7.0V

Notice: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

READ OPERATION

D.C. CHARACTERISTICS $0°C \leq T_A \leq +70°C$

Symbol	Parameter	Limits			Units	Test Conditions
		Min	Typ(2)	Max		
I_{LI}	Input Load Current			10	μA	V_{IN} = 0V to V_{CC}
I_{LO}	Output Leakage Current			10	μA	V_{OUT} = 0V to V_{CC}
I_{SB}(4)	V_{CC} Current Standby		20	40	mA	$\overline{CE}$ = V_{IH}
I_{CC_1}(4)	V_{CC} Current Active		90	125	mA	$\overline{CE}$ = $\overline{OE}/V_{PP}$ = V_{IL}
V_{IL}	Input Low Voltage	−0.1		+0.8	V	
V_{IH}	Input High Voltage	2.0		V_{CC} + 1	V	
V_{OL}	Output Low Voltage			0.45	V	I_{OL} = 2.1 mA
V_{OH}	Output High Voltage	2.4			V	I_{OH} = −400 μA

A.C. CHARACTERISTICS $0°C \leq T_A \leq +70°C$

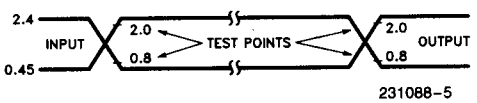
Versions(5, 6)	$V_{CC} \pm 5\%$	27512-170V05		27512-2		27512		27512-3		Units	Test Conditions
	$V_{CC} \pm 10\%$			27512-20 27512-200V10		27512-25		27512-30			
Symbol	**Parameter**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**		
t_{ACC}	Address to Output Delay		170		200		250		300	ns	$\overline{CE} = \overline{OE}/V_{PP} = V_{IL}$
t_{CE}	$\overline{CE}$ to Output Delay		170		200		250		300	ns	$\overline{OE}/V_{PP} = V_{IL}$
t_{OE}	$\overline{OE}/V_{PP}$ to Output Delay		60		75		100		120	ns	$\overline{CE} = V_{IL}$
t_{DF}(3)	$\overline{OE}/V_{PP}$ High to Output Float	0	50	0	55	0	60	0	105	ns	$\overline{CE} = V_{IL}$
t_{OH}(3)	Output Hold from Addresses $\overline{CE}$ or $\overline{OE}/V_{PP}$ Whichever Occurred First	0		0		0		0		ns	$\overline{CE} = \overline{OE}/V_{PP} = V_{IL}$

NOTES:
1. V_{CC} must be applied simultaneously or before $\overline{OE}/V_{PP}$ and removed simultaneously or after $\overline{OE}/V_{PP}$.
2. Typical values are for $T_A = 25°C$ and nominal supply voltages.
3. This parameter is only sampled and is not 100% tested. Output Float is defined as the point where data is no longer driven—see timing diagram.
4. The maximum current value is with outputs O_0–O_7 unloaded.
5. Packaging options: No prefix = Cerdip.
6. All products with the 6-digit speed identifier are produced on compacted HMOS II-E technology.

CAPACITANCE[2] $T_A = 25°C$, f = 1 MHz

Symbol	Parameter	Typ[1]	Max	Units	Conditions
C_{IN}	Input Capacitance	4	6	pF	V_{IN} = 0V
C_{OUT}	Output Capacitance	8	12	pF	V_{OUT} = 0V
$C_{\overline{OE}}/V_{PP}$	$\overline{OE}/V_{PP}$ Capacitance	18	25	pF	V_{IN} = 0V

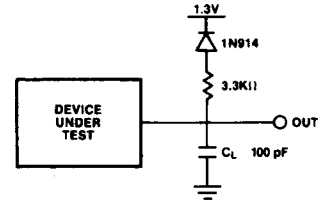
A.C. TESTING INPUT/OUTPUT WAVEFORM



231088-5

A.C. Testing: Inputs are driven at 2.4V for a Logic "1" and 0.45V for a Logic "0". Timing measurements are made at 2.0V for a Logic "1" and 0.8V for a Logic "0".

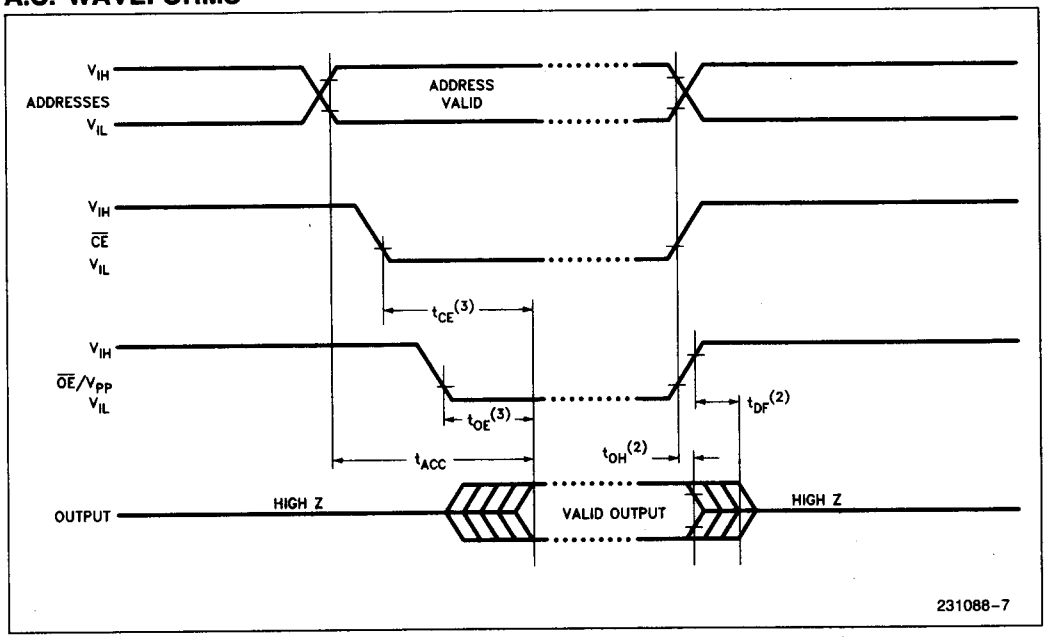
A.C. TESTING LOAD CIRCUIT



231088-6

C_L = 100 pF
C_L Includes Jig Capacitance

A.C. WAVEFORMS



231088-7

NOTES:
1. Typical values are for T_A = 25°C and nominal supply voltages.
2. This parameter is only sampled and is not 100% tested.
3. $\overline{OE}/V_{PP}$ may be delayed up to t_{CE}—t_{OE} after the falling edge of $\overline{CE}$ without impact on t_{CE}.

DEVICE OPERATION

The modes of operation of the 27512 are listed in Table 1. A single 5V power supply is required in the read mode. All inputs are TTL levels except for $\overline{OE}/V_{PP}$ and 12V on A9 for inteligent identifier mode.

Read Mode

The 27512 has two control functions, both of which must be logically active in order to obtain data at the outputs. Chip Enable ($\overline{CE}$) is the power control and should be used for device selection. Output Enable ($\overline{OE}/V_{PP}$) is the output control and should be used to gate data from the output pins, independent of device selection. Assuming that addresses are stable, the address access time (t_{ACC}) is equal to the delay from $\overline{CE}$ to output (t_{CE}). Data is available at the outputs after a delay of t_{OE} from the falling edge of $\overline{OE}$, assuming that $\overline{CE}$ has been low and addresses have been stable for at least t_{ACC}-t_{OE}.

Standby Mode

The 27512 has a standby mode which reduces the maximum active current from 125 mA to 40 mA. The 27512 is placed in the standby mode by applying a TTL-high signal to the $\overline{CE}$ input. When in standby mode, the outputs are in a high impedance state, independent of the $\overline{OE}/V_{PP}$ input.

Two Line Output Control

Because EPROMs are usually used in larger memory arrays, Intel has provided 2 control lines which accommodate this multiple memory connection. The two control lines allow for:

a) the lowest possible memory power dissipation, and

b) complete assurance that output bus contention will not occur.

To use these two control lines most efficiently, $\overline{CE}$ should be decoded and used as the primary device selecting function, while $\overline{OE}/V_{PP}$ should be made a common connection to all devices in the array and connected to the $\overline{READ}$ line from the system control bus. This assures that all deselected memory devices are in their low power standby mode and that the output pins are active only when data is desired from a particular memory device.

SYSTEM CONSIDERATIONS

The power switching characteristics of EPROMs require careful decoupling of the devices. The supply current, I_{CC}, has three segments that are of interest to the system designer—the standby current level, the active current level, and the transient current peaks that are produced by the falling and rising edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitive and inductive loading of the device. The associated transient voltage peaks can be suppressed by complying with Intel's Two-Line Control and by properly selected decoupling capacitors. It is recommended that a 0.1 μF ceramic capacitor be used on every device between V_{CC} and GND. This should be a high frequency capacitor of low inherent inductance and should be placed as close to the device as possible. In addition, a 4.7 μF bulk electrolytic capacitor should be used between V_{CC} and GND for every eight devices. The bulk capacitor should be located near where the power supply is connected to the array. The purpose of the bulk capacitor is to overcome the voltage droop caused by the inductive effects of PC board traces. This inductive effect should be further minimized through special layout considerations such as larger traces and gridding (refer to High Speed Memory System Design Using the 2147H, AP-74). In particular, the V_{SS} (Ground) plane should be as stable as possible.

Table 1. Operating Modes

Mode \ Pins	$\overline{CE}$	$\overline{OE}/V_{PP}$	A_9	A_0	V_{CC}	Outputs
Read	V_{IL}	V_{IL}	X(1)	X	5.0V	D_{OUT}
Output Disable	V_{IL}	V_{IH}	X	X	V_{CC}	High Z
Standby	V_{IH}	X	X	X	V_{CC}	High Z
Program	V_{IL}	V_{PP}(3)	X	X	6.0V	D_{IN}
Verify	V_{IL}	V_{IL}	X	X	6.0V	D_{OUT}
Program Inhibit	V_{IH}	V_{PP}(3)	X	X	6.0V	High Z
Inteligent Identifier(4) —Manufacturer	V_{IL}	V_{IL}	V_H(2)	V_{IL}	5.0V	89H
Inteligent Identifier(4) —Device	V_{IL}	V_{IL}	V_H(2)	V_{IH}	5.0V	0DH

NOTES:
1. X can be V_{IH} or V_{IL}.
2. V_H = 12.0V ±0.5V.
3. V_{PP} = 12.5 ±0.5V.
4. A_1–A_8, A_{10}–A_{13} = V_{IL}; A_{14}, A_{15} = V_{IH}.

PROGRAMMING MODES

Caution: Exceeding 14.0V on $\overline{OE}/V_{PP}$ will permanently damage the device.

Initially, and after each erasure, all bits of the EPROM are in the "1" state. Data is introduced by selectively programming "0s" into the desired bit locations. Although only "0s" will be programmed, both "1s" and "0s" can be present in the data word. The only way to change a "0" to a "1" is by ultraviolet light erasure (Cerdip EPROMs).

The EPROM is in the programming mode when the $\overline{OE}/V_{PP}$ input is raised to its programming voltage (see Table 2) and $\overline{CE}$ is at TTL-low. The data to be programmed is applied 8 bits in parallel to the data output pins. The levels required for the address and data inputs are TTL.

Program Inhibit

Programming of multiple 25712s in parallel with different data is easily accomplished by using the Program Inhibit mode. A high-level $\overline{CE}$ input inhibits the other 27512s from being programmed.

Except for $\overline{CE}$, all inputs of the parallel 27512s may be common. A TTL low-level pulse applied to the $\overline{CE}$ input with $\overline{OE}/V_{PP}$ at its programming voltage will program the selected 27512.

Verify

A verify (read) should be performed on the programmed bits to determine that they have been correctly programmed. The verify is performed with $\overline{OE}/V_{PP}$ and $\overline{CE}$ at V_{IL} and V_{CC} is at its programming voltage. Data should be verified t_{DV} after the falling edge of $\overline{CE}$.

inteligent Identifier™ Mode

The inteligent Identifier Mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional in the 25°C ±5°C ambient temperature range that is required when programming the device.

To activate this mode, the programming equipment must force 11.5V to 12.5V on address line A9 of the EPROM. Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 from V_{IL} to V_{IH}. All other address lines must be held at V_{IL} during the inteligent Identifier Mode, except for A14 and A15 which should be held high.

Byte 0 (A0 = V_{IL}) represents the manufacturer code and byte 1 (A0 = V_{IH}) the device identifier code. These two identifier bytes are given in Table 1.

ERASURE CHARACTERISTICS (FOR CERDIP EPROMS)

The erasure characteristics are such that erasure begins to occur upon exposure to light with wavelengths shorter than approximately 4000 Angstroms (Å). It should be noted that sunlight and certain types of fluorescent lamps have wavelengths in the 3000–4000Å range. Data show that constant exposure to room level fluorescent lighting could erase the EPROM in approximately 3 years, while it would take approximately 1 week to cause erasure when exposed to direct sunlight. If the device is to be exposed to these types of lighting conditions for extended periods of time, opaque labels should be placed over the window to prevent unintentional erasure.

The recommended erasure procedure is exposure to shortwave ultraviolet light which has a wavelength of 2537 Angstroms (Å). The integrated dose (i.e., UV intensity × exposure time) for erasure should be a minimum of 15 Wsec/cm^2. The erasure time with this dosage is approximately 15 to 20 minutes using an ultraviolet lamp with a 12000 μW/cm^2 power rating. The EPROM should be placed within 1 inch of the lamp tubes during erasure. The maximum integrated dose an EPROM can be exposed to without damage is 7258 Wsec/cm^2 (1 week @ 12000 μW/cm^2). Exposure of the device to high intensity UV light for longer periods may cause permanent damage.

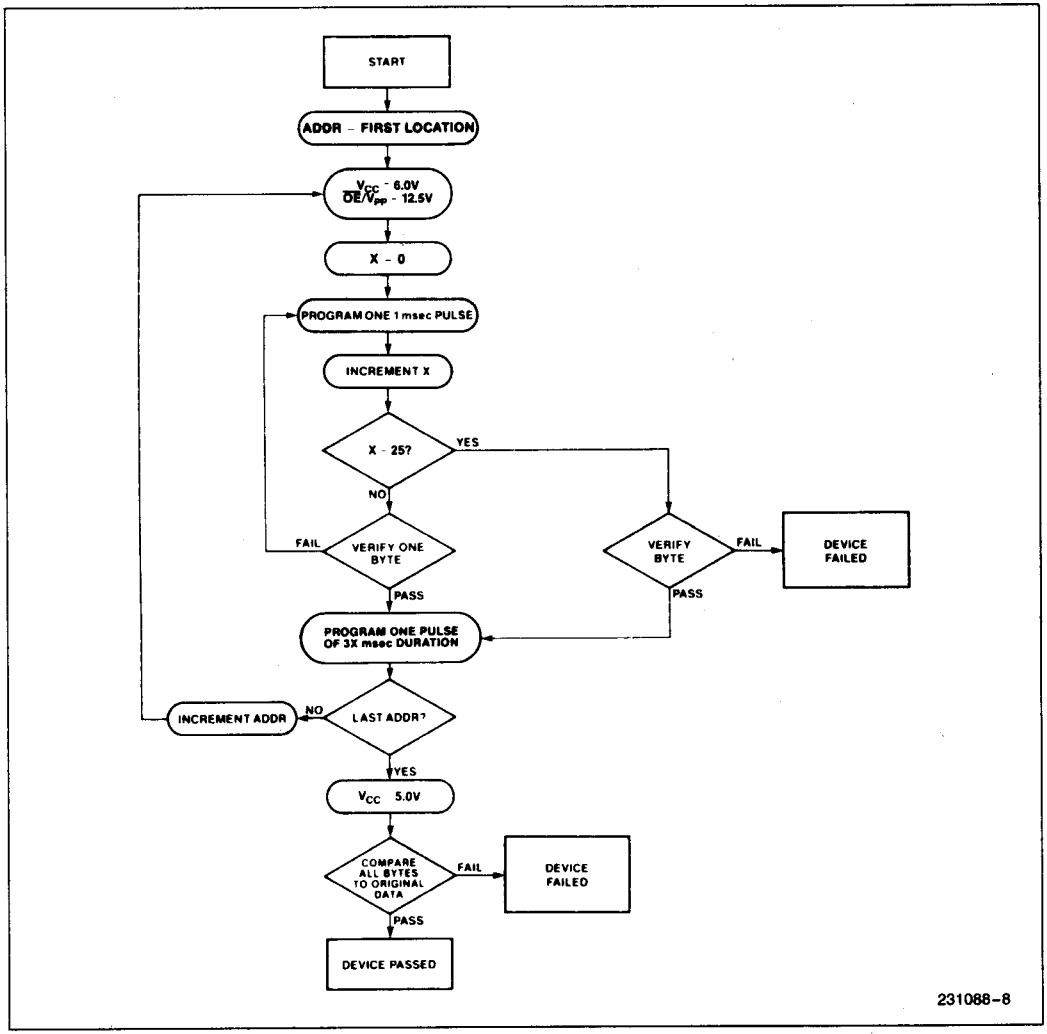


Figure 5. int$_e$ligent Programming™ Flowchart

int$_e$ligent Programming™ Algorithm

The int$_e$ligent Programming Algorithm programs Intel EPROMs using an efficient and reliable method particularly suited to the production programming environment. Typical programming time for individual devices are on the order of six minutes. Actual programming times may vary due to differences in programming equipment. Programming reliability is also ensured as the incremental program margin of each byte is continually monitored to determine when it has been successfully programmed. A flowchart of the int$_e$ligent Programming Algorithm is shown in Figure 4.

The int$_e$ligent Programming Algorithm utilizes two different pulse types: initial and overprogram. The duration of the initial pulse(s) is one millisecond, which will then be followed by a longer overprogram pulse of length 3X msec. X is an iteration counter and is equal to the number of the initial one millisecond pulses applied to a particular location, before a correct verify occurs. Up to 25 one-millisecond pulses per byte are provided for before the overprogram pulse is applied. ***The entire sequence of program pulses and byte verifications is performed at V_{CC} = 6.0V.*** When the int$_e$ligent Programming cycle has been completed, all bytes should be compared to the original data with V_{CC} = 5.0V.

TABLE 2. D.C. PROGRAMMING CHARACTERISTICS

T_A = 25 ±5°C

Symbol	Parameter	Limits			Test Conditions (Note 1)
		Min	Max	Unit	
I_{LI}	Input Current (All Inputs)		10	μA	$V_{IN} = V_{IL}$ or V_{IH}
V_{IL}	Input Low Level (All Inputs)	−0.1	0.8	V	
V_{IH}	Input High Level	2.0	V_{CC} +1	V	
V_{OL}	Output Low Voltage During Verify		0.45	V	I_{OL} 2.1 mA
V_{OH}	Output High Voltage During Verify	2.4		V	I_{OH} = −400 μA
I_{CC2}(4)	V_{CC} Supply Current (Program & Verify)		125	mA	
I_{PP2}(4)	V_{PP} Supply Current (Program)		40	mA	$\overline{CE} = V_{IL}$, $\overline{OE}/V_{PP} = V_{PP}$
V_{ID}	A_9 intelligent Identifier Voltage	11.5	12.5	V	
V_{PP}	intelligent Programming Algorithm	12.0	13.0	V	
V_{CC}	intelligent Programming Algorithm	5.75	6.25	V	

A.C. PROGRAMMING CHARACTERISTICS

T_A = 25 ±5°C

Symbol	Parameter	Limits				Conditions* (Note 1)
		Min	Typ	Max	Unit	
t_{AS}	Address Setup Time	2			μs	
t_{OES}	$\overline{OE}/V_{PP}$ Setup Time	2			μs	
t_{DS}	Data Setup Time	2			μs	
t_{AH}	Address Hold Time	0			μs	
t_{DH}	Data Hold Time	2			μs	
t_{DFP}	Output Enable to Output Float Delay	0		130	ns	(Note 3)
t_{VCS}	V_{CC} Setup Time	2			μs	(Note 1)
t_{PW}	$\overline{CE}$ Initial Program Pulse Width	0.95	1.0	1.05	ms	intelligent Programming
t_{OPW}	$\overline{CE}$ Overprogram Pulse Width	2.85		78.75	ms	(Note 2)
t_{OEH}	$\overline{OE}/V_{PP}$ Hold Time	2			μs	
t_{DV}	Data Valid from $\overline{CE}$			1	μs	
t_{VR}	$\overline{OE}/V_{PP}$ Recovery Time	2			μs	
t_{PRT}	$\overline{OE}/V_{PP}$ Pulse Rise Time During Programming	50			ns	

***A.C. CONDITIONS OF TEST**

Input Rise and Fall Times (10% to 90%) ..... 20 ns

Input Pulse Levels ..... 0.45V to 2.4V

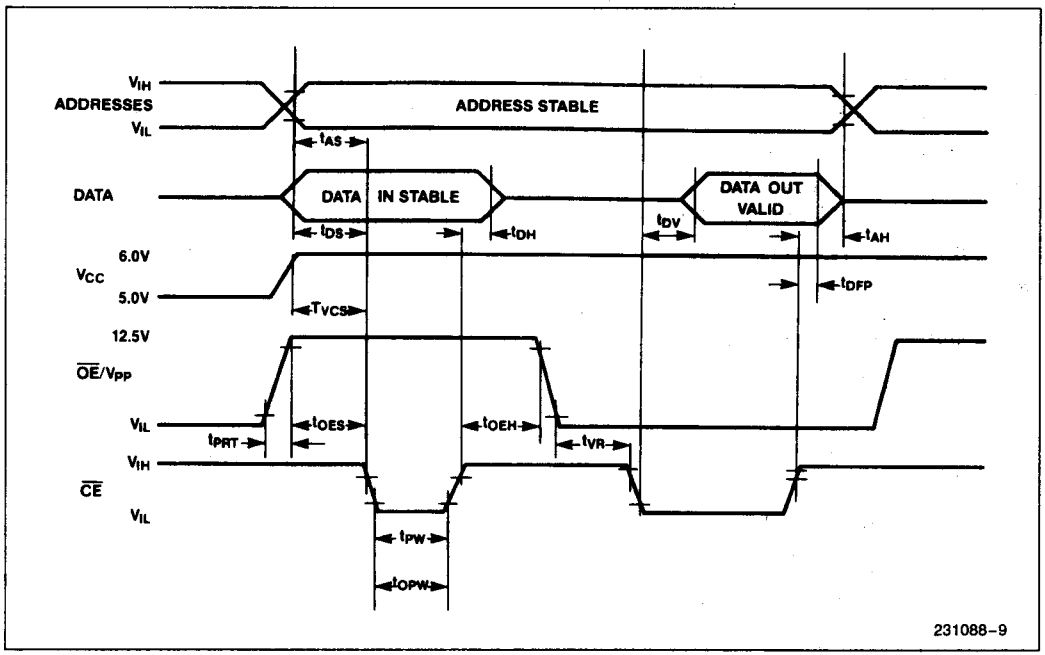
Input Timing Reference Level ..... 0.8V and 2.0V

Output Timing Reference Level ..... 0.8V and 2.0V

NOTES:

1. V_{CC} must be applied simultaneously or before $\overline{OE}/V_{PP}$ and removed simultaneously or after $\overline{OE}/V_{PP}$.
2. The length of the overprogram pulse (intelligent Programming Algorithm) may vary from 2.85 msec to 78.75 msec as a function of the iteration counter value X.
3. This parameter is only sampled and is not 100% tested. Output Float is defined as the point where data is no longer driven—see timing diagram.
4. The maximum current value is with outputs O_0 to O_7 unloaded.

PROGRAMMING WAVEFORMS



NOTES:
1. The Input Timing Reference Level is 0.8V for V_{IL} and 2.0V for a V_{IH}.
2. t_{OE} and t_{DFP} are characteristics of the device but must be accommodated by the programmer.

REVISION HISTORY

Number	Description
07	Revised Pin Configuration, Express Options D.C. Characteristics-I_{LI} Test Conditions-V_{IN} = 0V to V_{CC} D.C. Characteristics-I_{LO} Test Conditions-V_{OUT} = 0V to V_{CC} Deleted -200V05 Speed Bin